

# Yu-Ning Wu

## List of Publications by Year in descending order

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33  
papers

551  
citations

623574

14  
h-index

642610

23  
g-index

33  
all docs

33  
docs citations

33  
times ranked

854  
citing authors



#	ARTICLE	IF	CITATIONS
19	First-principles calculations reveal controlling principles for carrier mobilities in semiconductors. Semiconductor Science and Technology, 2016, 31, 115016.	1.0	8
20	$\text{MGa}_2\text{BO}_7\text{:Bi}^{3+}$ , $\text{Al}^{3+}$ (M = Sr, Ba) blue phosphors with a quantum yield of 99% and negative thermal quenching. Inorganic Chemistry Frontiers, 2021, 8, 4257-4266.	3.0	7
21	First-principles identification of $\text{V}_i\text{-}\hat{\text{A}}\text{Cu}_i$ defect cluster in cuprous iodide: origin of red light photoluminescence. Nanotechnology, 2022, 33, 195203.	1.3	7
22	Temperature effect on charge-state transition levels of defects in semiconductors. Physical Review B, 2022, 105, .	1.1	7
23	Theoretical and experimental study of temperature effect on electronic and optical properties of $\text{TiO}_2$ : Comparing rutile and anatase. Journal of Physics Condensed Matter, 2020, 32, 405705.	0.7	5
24	First-principles calculations of Fe-doped monolayer C60 on h-BN/Ni(111) surface. Journal of Chemical Physics, 2010, 132, 074702.	1.2	3
25	Accurate projected augmented wave datasets for $\text{BaFe}_2\text{As}_2$ . New Journal of Physics, 2010, 12, 123029.	1.2	3
26	Enhancement of Ag cluster mobility on Ag surfaces by chloridation. Journal of Chemical Physics, 2012, 137, 184705.	1.2	3
27	First-principles identification of deep energy levels of sulfur impurities in silicon and their carrier capture cross sections. Journal Physics D: Applied Physics, 2021, 54, 335103.	1.3	3
28	Wu, Zhang, and Pantelides Reply:. Physical Review Letters, 2018, 120, 039604.	2.9	2
29	Bandgap Engineering through Halide Double-Perovskite Alloys: A High-Throughput First-Principles Study. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100343.	1.2	2
30	Enhancing neutron radiation resistance of silicon-based semiconductor devices through isotope separation and enrichment. Radiation Effects and Defects in Solids, 2021, 176, 419-430.	0.4	2
31	Defects and dopants in zinc-blende aluminum arsenide: a first-principles study. New Journal of Physics, 2021, 23, 013018.	1.2	1
32	Formation of $\text{Bi}^{\cdot}$ Dimers in Heavily $\text{Bi}^{\cdot}$ -Doped Lead Halide Perovskites: Origin of Carrier Density Saturation. Physical Review Applied, 2022, 17, .	1.5	1
33	Temperature-dependent electronic structure of $\beta$ -phase $\text{CuI}$ : first-principles insights. Journal of Physics Condensed Matter, 2021, , .	0.7	0